

IN THE CLAIMS:

Claims 1-5 and 9-14 were previously cancelled. Claims 6, 15 and 18 have been amended herein. All of the pending claims are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

Listing of Claims:

1.-5. (Cancelled)

6. (Currently amended) A capacitor assembly ~~comprising~~ comprising:
a storage node extending within an insulative layer, wherein the storage node is next to a layer
comprising silicon, about 2% to about 20% by weight carbon and about 5% to about 75%
by weight oxygen;
a second electrode proximate the storage node; and
a dielectric layer between the storage node and the second electrode.

7. (Original) The capacitor assembly of claim 6, wherein the storage node is next to
a layer comprising about 20% to about 65% by weight silicon, about 0% to about 30% by weight
nitrogen, about 10% to about 20% by weight carbon, and about 5% to about 25% by weight
oxygen.

8. (Original) The capacitor assembly of claim 6, wherein the storage node is next to
a layer comprising about 20% to about 65% by weight silicon, about 0% to about 15% by weight
nitrogen, about 2% to about 10% by weight carbon, and about 40% to about 75% by weight
oxygen.

9.-14. (Cancelled)

15. (Currently amended) An assembly comprising:
a substrate;
a layer comprising silicon, about 2% to about 20% by weight carbon and about 5% to about 75%
by weight oxygen; and
a photoresist masking layer.

16. (Original) The assembly of claim 15, wherein the layer comprises about 20% to
about 65% by weight silicon, about 10% to about 20% by weight carbon, about 5% to about 25%
by weight oxygen and about 0% to about 30% by weight nitrogen.

17. (Original) The assembly of claim 15, wherein the layer comprises about 20% to
about 65% by weight silicon, about 2% to about 10% by weight carbon, about 40% to about 75%
by weight oxygen and about 0% to about 15% by weight nitrogen.

18. (Currently amended) The assembly of claim 15, wherein the photoresist masking
layer is a patterned photoresist masking layer.

19. (Previously presented) The assembly of claim 15, wherein the substrate is a
monocrystalline wafer.

20. (Previously presented) The capacitor of claim 6, wherein the storage node
comprises conductively doped silicon.

21. (Previously presented) The capacitor of claim 6, wherein the insulative layer
comprises silicon oxide or silicon nitride.

22. (Previously presented) The capacitor of claim 6, wherein the dielectric layer
comprises silicon dioxide or silicon nitride.

IN THE DRAWINGS:

The attached sheet of replacement drawings includes a change to FIG. 4. This sheet replaces the original sheet including FIG. 4.

Specifically, FIG. 4 has been revised to change the reference numeral "30" to --28--, as shown in the attached annotated drawing sheet. No new matter has been added.